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# HM628128D Series

1 M SRAM (128-kword × 8-bit)

# HITACHI

ADE-203-996 (Z)  
Preliminary, Rev. 0.0  
Jan. 20, 1999

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## Description

The Hitachi HM628128D Series is 1-Mbit static RAM organized 131,072-kword × 8-bit. HM628128D Series has realized higher density, higher performance and low power consumption by employing Hi-CMOS process technology. The HM628128D Series offers low power standby power dissipation; therefore, it is suitable for battery backup systems. It has package variations of standard 32-pin plastic DIP, standard 32-pin plastic SOP and standard 32-pin plastic TSOPI.

## Features

- Single 5 V supply: 5 V ± 10%
- Access time: 55 ns/70 ns (max)
- Power dissipation
  - Active: 30 mW/MHz (typ)
  - Standby: 10 μW (typ)
- Completely static memory.
  - No clock or timing strobe required
- Equal access and cycle times
- Common data input and output
  - Three state output
- Directly TTL compatible all inputs
- Battery backup operation
  - 2 chip selection for battery backup

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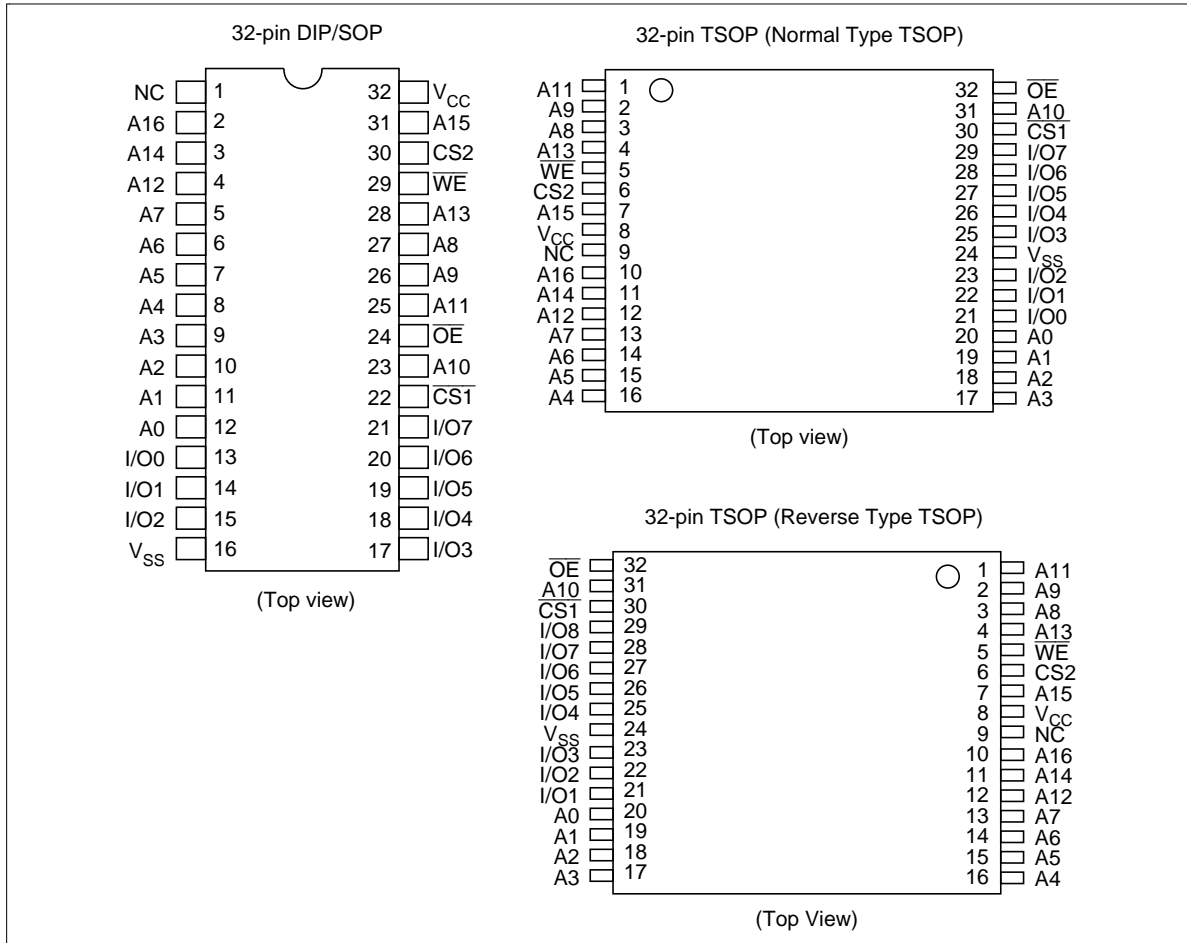
## HM628128D Series

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### Ordering Information

Type No.	Access time	Package
HM628128DLP-5	55 ns	600-mil 32-pin plastic DIP (DP-32)
HM628128DLP-7	70 ns	
HM628128DLP-5SL	55 ns	
HM628128DLP-7SL	70 ns	
HM628128DLP-5UL	55 ns	
HM628128DLP-7UL	70 ns	
HM628128DLFP-5	55 ns	525-mil 32-pin plastic SOP (FP-32D)
HM628128DLFP-7	70 ns	
HM628128DLFP-5SL	55 ns	
HM628128DLFP-7SL	70 ns	
HM628128DLFP-5UL	55 ns	
HM628128DLFP-7UL	70 ns	
HM628128DLTS-5	55 ns	8 × 13.4 mm 32-pin plastic TSOP I (TFP-32DC)
HM628128DLTS-7	70 ns	
HM628128DLTS-5SL	55 ns	
HM628128DLTS-7SL	70 ns	
HM628128DLTS-5UL	55 ns	
HM628128DLTS-7UL	70 ns	
HM628128DLT-5	55 ns	Normal-bend type 8 × 20 mm 32-pin plastic TSOP I (TFP-32D)
HM628128DLT-7	70 ns	
HM628128DLT-5SL	55 ns	
HM628128DLT-7SL	70 ns	
HM628128DLT-5UL	55 ns	
HM628128DLT-7UL	70 ns	
HM628128DLR-5	55 ns	Reverse-bend type 8 × 20 mm 32-pin plastic TSOP I (TFP-32DR)
HM628128DLR-7	70 ns	
HM628128DLR-5SL	55 ns	
HM628128DLR-7SL	70 ns	
HM628128DLR-5UL	55 ns	
HM628128DLR-7UL	70 ns	

## Pin Arrangement

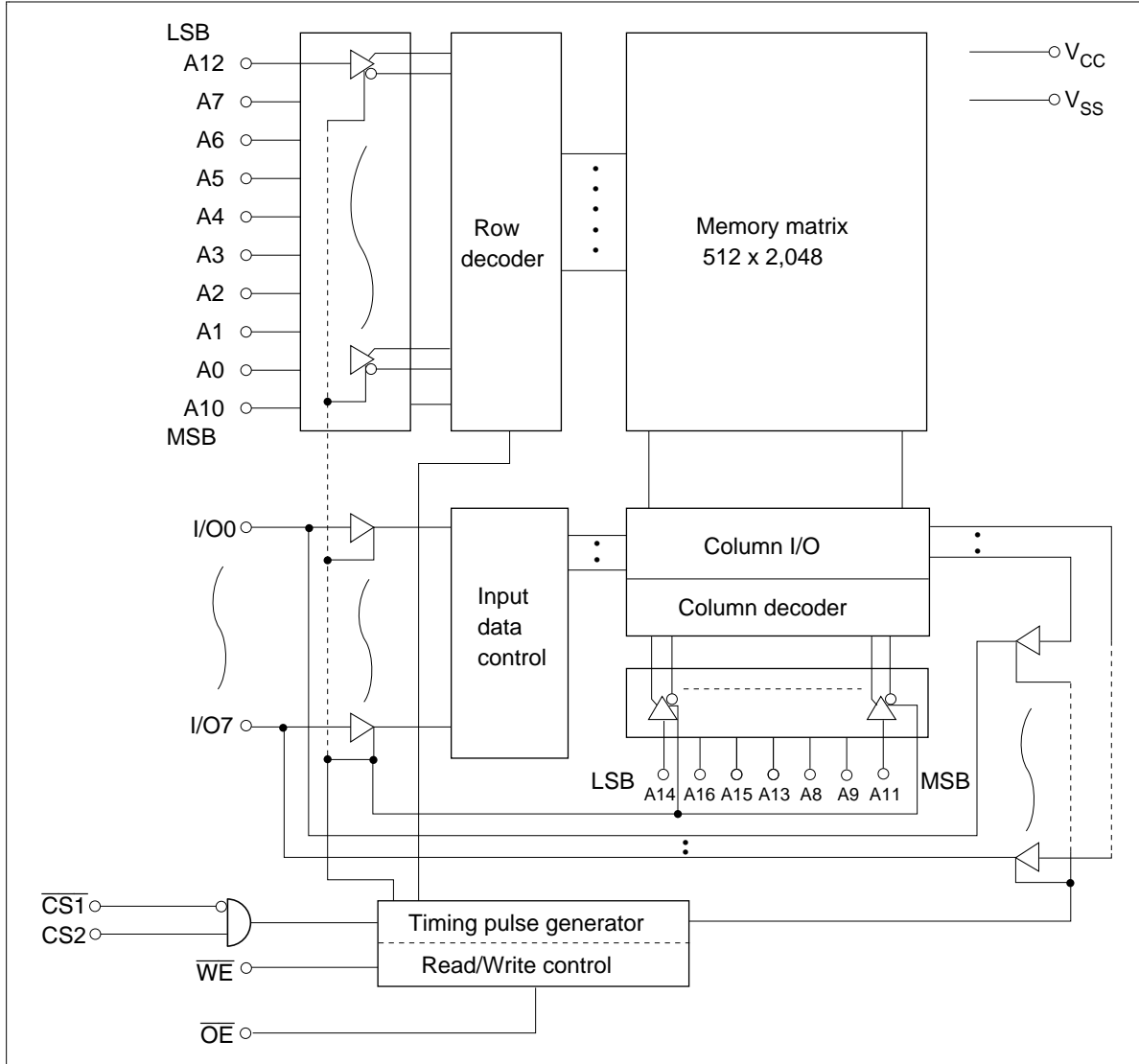


## Pin Description

Pin name	Function
A0 to A16	Address input
I/O0 to I/O7	Data input/output
$\overline{CS1}$	Chip select 1
CS2	Chip select 2
$\overline{WE}$	Write enable
$\overline{OE}$	Output enable
V <sub>cc</sub>	Power supply
V <sub>ss</sub>	Ground
NC	No connection

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## Block Diagram



**Operation Table**

$\overline{CS1}$	CS2	$\overline{WE}$	$\overline{OE}$	I/O	Operation
H	H	×	×	High-Z	Standby
L	L	×	×	High-Z	Standby
L	L	×	×	High-Z	Standby
L	H	H	L	Dout	Read
L	H	L	H	Din	Write
L	H	L	L	Din	Write
L	H	H	H	High-Z	Output disable

Note: H:  $V_{IH}$ , L:  $V_{IL}$ , ×:  $V_{IH}$  or  $V_{IL}$

**Absolute Maximum Ratings**

Parameter	Symbol	Value	Unit
Power supply voltage relative to $V_{SS}$	$V_{CC}$	-0.5 to +7.0	V
Terminal voltage on any pin relative to $V_{SS}$	$V_T$	-0.5* <sup>1</sup> to $V_{CC} + 0.3$ * <sup>2</sup>	V
Power dissipation	$P_T$	1.0	W
Storage temperature range	Tstg	-55 to +125	°C
Storage temperature range under bias	Tbias	-20 to +85	°C

Notes: 1.  $V_T$  min: -1.5 V for pulse half-width  $\leq$  30 ns  
 2. Maximum voltage is +7.0 V

**DC Operating Conditions**

Parameter	Symbol	Min	Typ	Max	Unit	Note
Supply voltage	$V_{CC}$	4.5	5.0	5.5	V	
	$V_{SS}$	0	0	0	V	
Input high voltage	$V_{IH}$	2.2	—	$V_{CC} + 0.3$	V	
Input low voltage	$V_{IL}$	-0.3	—	0.8	V	1
Ambient temperature range	Ta	-20	—	+70	°C	

Note: 1.  $V_{IL}$  min: -1.5 V for pulse half-width  $\leq$  30 ns

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### DC Characteristics

Parameter	Symbol	Min	Typ* <sup>1</sup>	Max	Unit	Test conditions
Input leakage current	$ I_{LI} $	—	—	1	$\mu\text{A}$	$V_{in} = V_{SS}$ to $V_{CC}$
Output leakage current	$ I_{LO} $	—	—	1	$\mu\text{A}$	$\overline{CS1} = V_{IH}$ or $CS2 = V_{IL}$ or $OE = V_{IH}$ or $\overline{WE} = V_{IL}$ , $V_{I/O} = V_{SS}$ to $V_{CC}$
Operating current	$I_{CC}$	—	—	15	$\text{mA}$	$\overline{CS1} = V_{IL}$ , $CS2 = V_{IH}$ , others = $V_{IH}/V_{IL}$ , $I_{I/O} = 0 \text{ mA}$
Average operating current	$I_{CC1}$	—	—	60	$\text{mA}$	Min cycle, duty = 100% $I_{I/O} = 0 \text{ mA}$ , $\overline{CS1} = V_{IL}$ , $CS2 = V_{IH}$ , Others = $V_{IH}/V_{IL}$
	$I_{CC2}$	—	6	20	$\text{mA}$	Cycle time = 1 $\mu\text{s}$ , duty = 100%, $I_{I/O} = 0 \text{ mA}$ , $\overline{CS1} \leq 0.2 \text{ V}$ , $CS2 \geq V_{CC} - 0.2 \text{ V}$ , $V_{IH} \geq V_{CC} - 0.2 \text{ V}$ , $V_{IL} \leq 0.2 \text{ V}$
Standby current	$I_{SB}$	—	—	2	$\text{mA}$	(1) $\overline{CS1} = V_{IH}$ , $CS2 = V_{IH}$ , or (2) $CS2 = V_{IL}$
	$I_{SB1}^{*2}$	—	2	100	$\mu\text{A}$	0 V $\leq V_{in}$ (1) 0 V $\leq CS2 \leq 0.2 \text{ V}$ or (2) $\overline{CS1} \geq V_{CC} - 0.2 \text{ V}$ , $CS2 \geq V_{CC} - 0.2 \text{ V}$
	$I_{SB1}^{*3}$	—	2	50	$\mu\text{A}$	
	$I_{SB1}^{*4}$	—	1	20	$\mu\text{A}$	
Output high voltage	$V_{OH}$	2.4	—	—	V	$I_{OH} = -1 \text{ mA}$
Output low voltage	$V_{OL}$	—	—	0.4	V	$I_{OL} = 2.1 \text{ mA}$

- Notes: 1. Typical values are at  $V_{CC} = 5.0 \text{ V}$ ,  $T_a = +25^\circ\text{C}$  and specified loading, and not guaranteed.  
 2. This characteristics is guaranteed only for L version.  
 3. This characteristics is guaranteed only for L-SL version.  
 4. This characteristics is guaranteed only for L-UL version.

### Capacitance ( $T_a = +25^\circ\text{C}$ , $f = 1 \text{ MHz}$ )

Parameter	Symbol	Typ	Max	Unit	Test conditions	Note
Input capacitance	$C_{in}$	—	8	$\text{pF}$	$V_{in} = 0 \text{ V}$	1
Input/output capacitance	$C_{I/O}$	—	10	$\text{pF}$	$V_{I/O} = 0 \text{ V}$	1

- Note: 1. This parameter is sampled and not 100% tested.

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**AC Characteristics** ( $T_a = -20$  to  $+70^\circ\text{C}$ ,  $V_{CC} = 5.0\text{ V} \pm 10\%$ , unless otherwise noted.)

### Test Conditions

- Input pulse levels:  $V_{IL} = 0.8\text{ V}$ ,  $V_{IH} = 2.4\text{ V}$
- Input rise and fall time: 5 ns
- Input timing reference levels: 1.5 V
- Output timing reference level: 1.5 V
- Output load: 1 TTL Gate+ CL (100 pF) (HM628128D-7)  
1 TTL Gate+ CL (50 pF) (HM628128D-5)  
(Including scope and jig)

### Read Cycle

HM628128D							
		-5		-7			
Parameter	Symbol	Min	Max	Min	Max	Unit	Notes
Read cycle time	$t_{RC}$	55	—	70	—	ns	
Address access time	$t_{AA}$	—	55	—	70	ns	
Chip select access time	$t_{ACS1}$	—	55	—	70	ns	
	$t_{ACS2}$	—	55	—	70	ns	
Output enable to output valid	$t_{OE}$	—	30	—	35	ns	
Output hold from address change	$t_{OH}$	10	—	10	—	ns	
Chip selection to output in low-Z	$t_{CLZ1}$	10	—	10	—	ns	2, 3
	$t_{CLZ2}$	10	—	10	—	ns	2, 3
Output enable to output in low-Z	$t_{OLZ}$	5	—	5	—	ns	2, 3
Chip deselection to output in high-Z	$t_{CHZ1}$	0	20	0	25	ns	1, 2, 3
	$t_{CHZ2}$	0	20	0	25	ns	1, 2, 3
Output disable to output in high-Z	$t_{OHZ}$	0	20	0	25	ns	1, 2, 3

## HM628128D Series

### Write Cycle

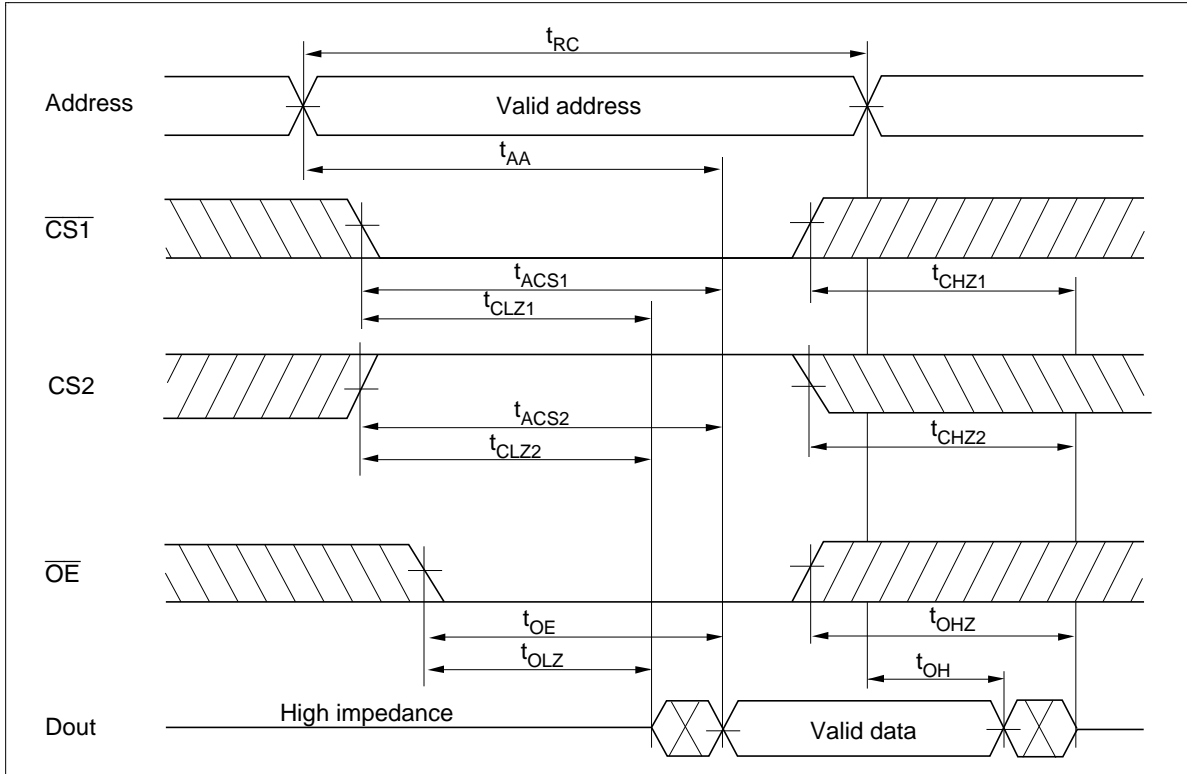
HM628128D							
		-5		-7			
Parameter	Symbol	Min	Max	Min	Max	Unit	Notes
Write cycle time	$t_{WC}$	55	—	70	—	ns	
Address valid to end of write	$t_{AW}$	50	—	60	—	ns	
Chip selection to end of write	$t_{CW}$	50	—	60	—	ns	5
Write pulse width	$t_{WP}$	40	—	50	—	ns	4, 13
Address setup time	$t_{AS}$	0	—	0	—	ns	6
Write recovery time	$t_{WR}$	0	—	0	—	ns	7
Data to write time overlap	$t_{DW}$	20	—	25	—	ns	
Data hold from write time	$t_{DH}$	0	—	0	—	ns	
Output active from output in high-Z	$t_{OW}$	5	—	5	—	ns	2
Output disable to output in high-Z	$t_{OHZ}$	0	20	0	25	ns	1, 2, 8
$\overline{WE}$ to output in high-Z	$t_{WHZ}$	0	20	0	25	ns	1, 2, 8

- Notes:
- $t_{CHZ}$ ,  $t_{OHZ}$  and  $t_{WHZ}$  are defined as the time at which the outputs achieve the open circuit conditions and are not referred to output voltage levels.
  - This parameter is sampled and not 100% tested.
  - At any given temperature and voltage condition,  $t_{HZ}$  max is less than  $t_{LZ}$  min both for a given device and from device to device.
  - A write occurs during the overlap ( $t_{WP}$ ) of a low  $\overline{CS1}$ , a high CS2, and a low  $\overline{WE}$ . A write begins at the later transition of  $\overline{CS1}$  going low, CS2 going high, or  $\overline{WE}$  going low. A write ends at the earlier transition of  $\overline{CS1}$  going high, CS2 going low, or  $\overline{WE}$  going high.  $t_{WP}$  is measured from the beginning of write to the end of write.
  - $t_{CW}$  is measured from  $\overline{CS1}$  going low or CS2 going high to the end of write.
  - $t_{AS}$  is measured from the address valid to the beginning of write.
  - $t_{WR}$  is measured from the earlier of  $\overline{WE}$  or  $\overline{CS1}$  going high or CS2 going low to the end of write cycle.
  - During this period, I/O pins are in the output state; therefore, the input signals of the opposite phase to the outputs must not be applied.
  - If the  $\overline{CS1}$  goes low or CS2 going high simultaneously with  $\overline{WE}$  going low or after  $\overline{WE}$  going low, the output remain in a high impedance state.
  - Dout is the same phase of the write data of this write cycle.
  - Dout is the read data of next address.
  - If  $\overline{CS1}$  is low and CS2 high during this period, I/O pins are in the output state. Therefore, the input signals of the opposite phase to the outputs must not be applied to them.
  - In the write cycle with  $\overline{OE}$  low fixed,  $t_{WP}$  must satisfy the following equation to avoid a problem of data bus contention.  $t_{WP} \geq t_{DW} \text{ min} + t_{WHZ} \text{ max}$



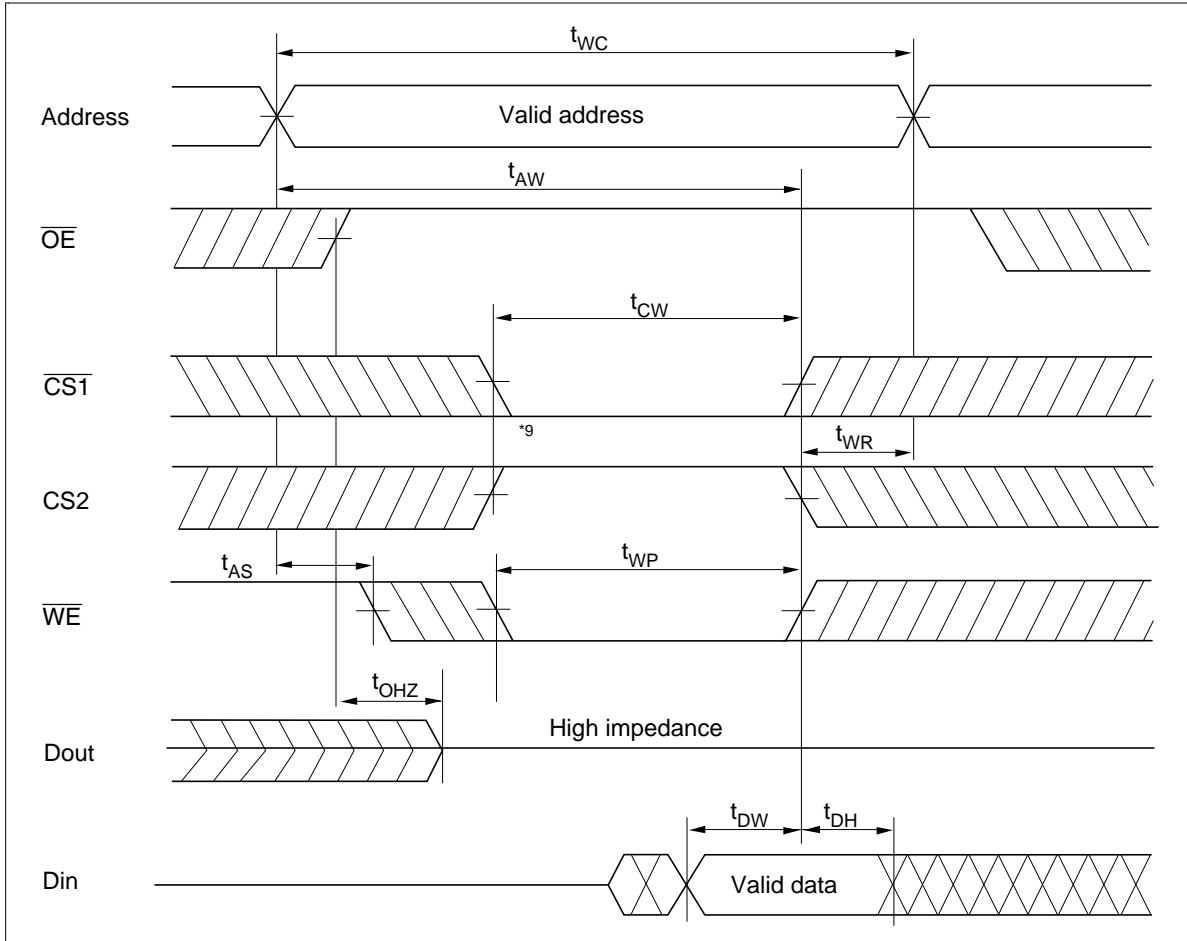
Timing Waveforms

Read Cycle ( $\overline{WE} = V_{IH}$ )

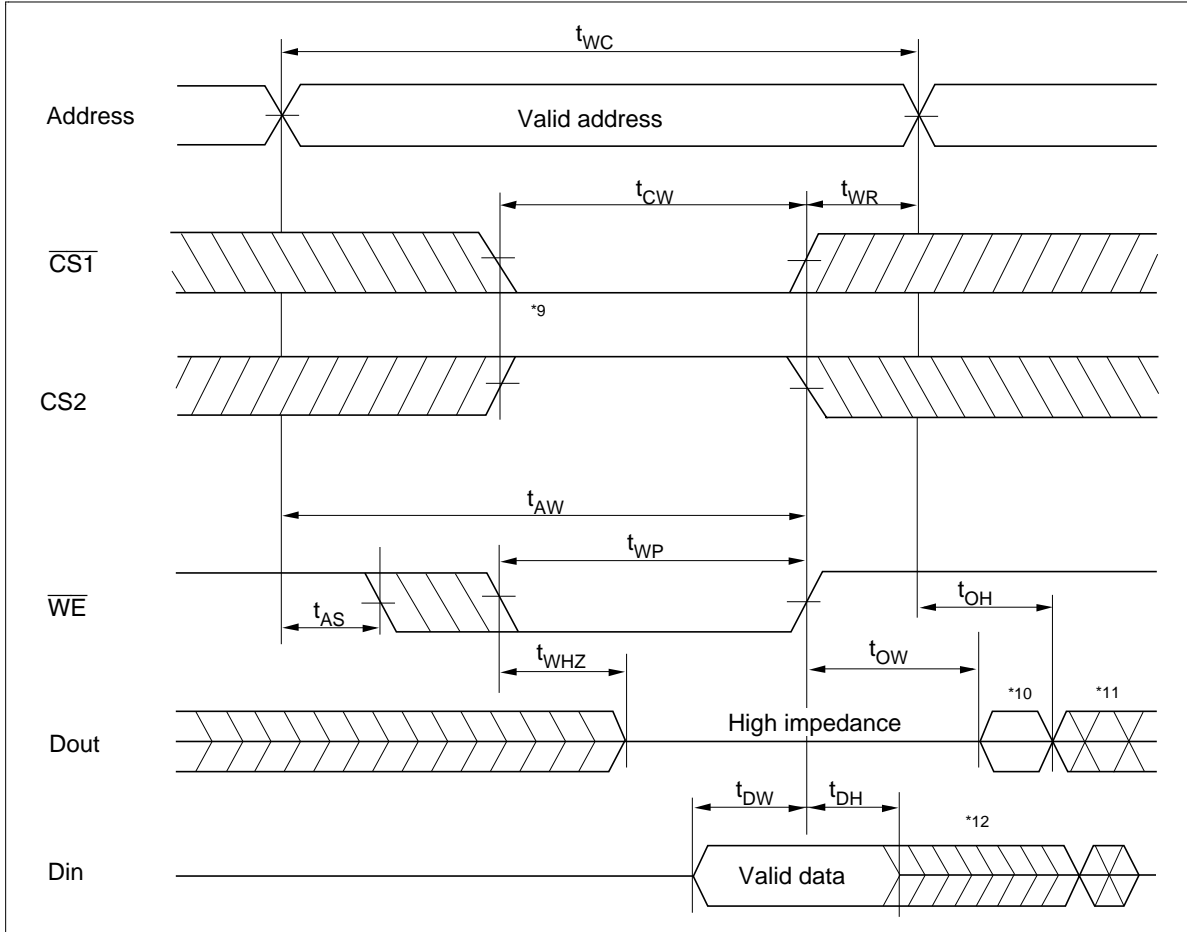


# HM628128D Series

## Write Cycle (1) ( $\overline{\text{OE}}$ Clock)



Write Cycle (2) ( $\overline{OE} = V_{IL}$ )



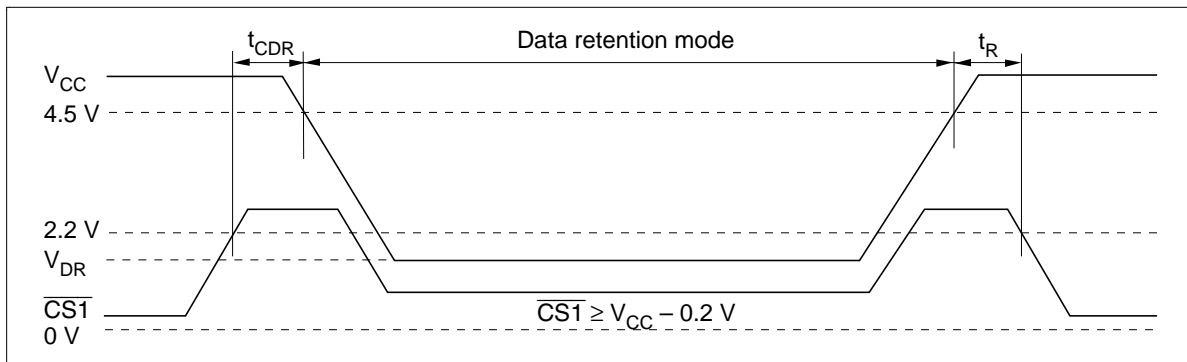
## HM628128D Series

### Low $V_{CC}$ Data Retention Characteristics ( $T_a = -20$ to $+70^\circ\text{C}$ )

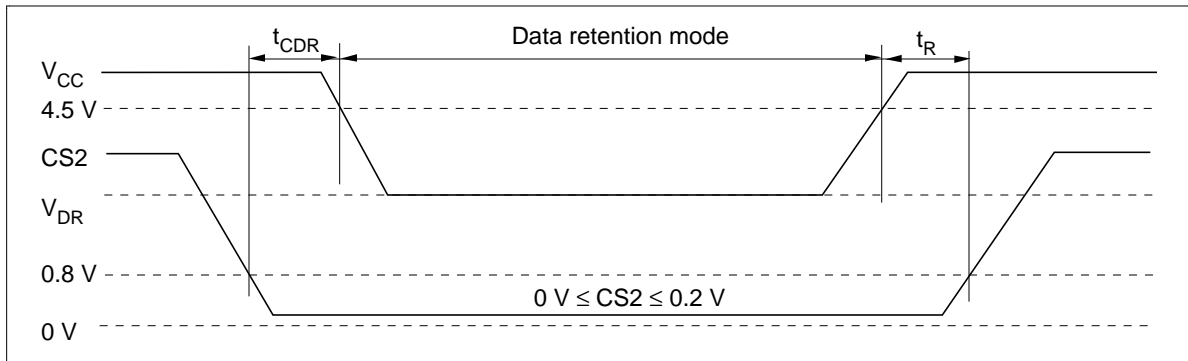
Parameter	Symbol	Min	Typ <sup>*5</sup>	Max	Unit	Test conditions <sup>*4</sup>
$V_{CC}$ for data retention	$V_{DR}$	2.0	—	—	V	$V_{in} \geq 0\text{V}$ (1) $0\text{V} \leq \text{CS2} \leq 0.2\text{V}$ or (2) $\text{CS2} \geq V_{CC} - 0.2\text{V}$ $\text{CS1} \geq V_{CC} - 0.2\text{V}$
Data retention current	$I_{CCDR}^{*1}$	—	1.0	50	$\mu\text{A}$	$V_{CC} = 3.0\text{V}$ , $V_{in} \geq 0\text{V}$ (1) $0\text{V} \leq \text{CS2} \leq 0.2\text{V}$ or (2) $\text{CS2} \geq V_{CC} - 0.2\text{V}$ , $\text{CS1} \geq V_{CC} - 0.2\text{V}$
	$I_{CCDR}^{*2}$	—	1.0	15	$\mu\text{A}$	
	$I_{CCDR}^{*3}$	—	0.5	10	$\mu\text{A}$	
Chip deselect to data retention time	$t_{CDR}$	0	—	—	ns	See retention waveform
Operation recovery time	$t_R$	$t_{RC}^{*6}$	—	—	ns	

- Notes:
1. This characteristic is guaranteed only for L-version, 20  $\mu\text{A}$  max. at  $T_a = -20$  to  $+40^\circ\text{C}$ .
  2. This characteristic is guaranteed only for L-SL-version, 3  $\mu\text{A}$  max. at  $T_a = -20$  to  $+40^\circ\text{C}$ .
  3. This characteristic is guaranteed only for L-UL-version, 1  $\mu\text{A}$  max. at  $T_a = -20$  to  $+40^\circ\text{C}$ .
  4. CS2 controls address buffer,  $\overline{\text{WE}}$  buffer,  $\overline{\text{CS1}}$  buffer,  $\overline{\text{OE}}$  buffer, and Din buffer. If CS2 controls data retention mode,  $V_{in}$  levels (address,  $\overline{\text{WE}}$ ,  $\overline{\text{OE}}$ ,  $\overline{\text{CS1}}$ , I/O) can be in the high impedance state. If  $\overline{\text{CS1}}$  controls data retention mode, CS2 must be  $\text{CS2} \geq V_{CC} - 0.2\text{V}$  or  $0\text{V} \leq \text{CS2} \leq 0.2\text{V}$ . The other input levels (address,  $\overline{\text{WE}}$ ,  $\overline{\text{OE}}$ , I/O) can be in the high impedance state.
  5. Typical values are at  $V_{CC} = 3.0\text{V}$ ,  $T_a = +25^\circ\text{C}$  and specified loading, and not guaranteed.
  6.  $t_{RC}$  = read cycle time.

### Low $V_{CC}$ Data Retention Timing Waveform (1) ( $\overline{\text{CS1}}$ Controlled)



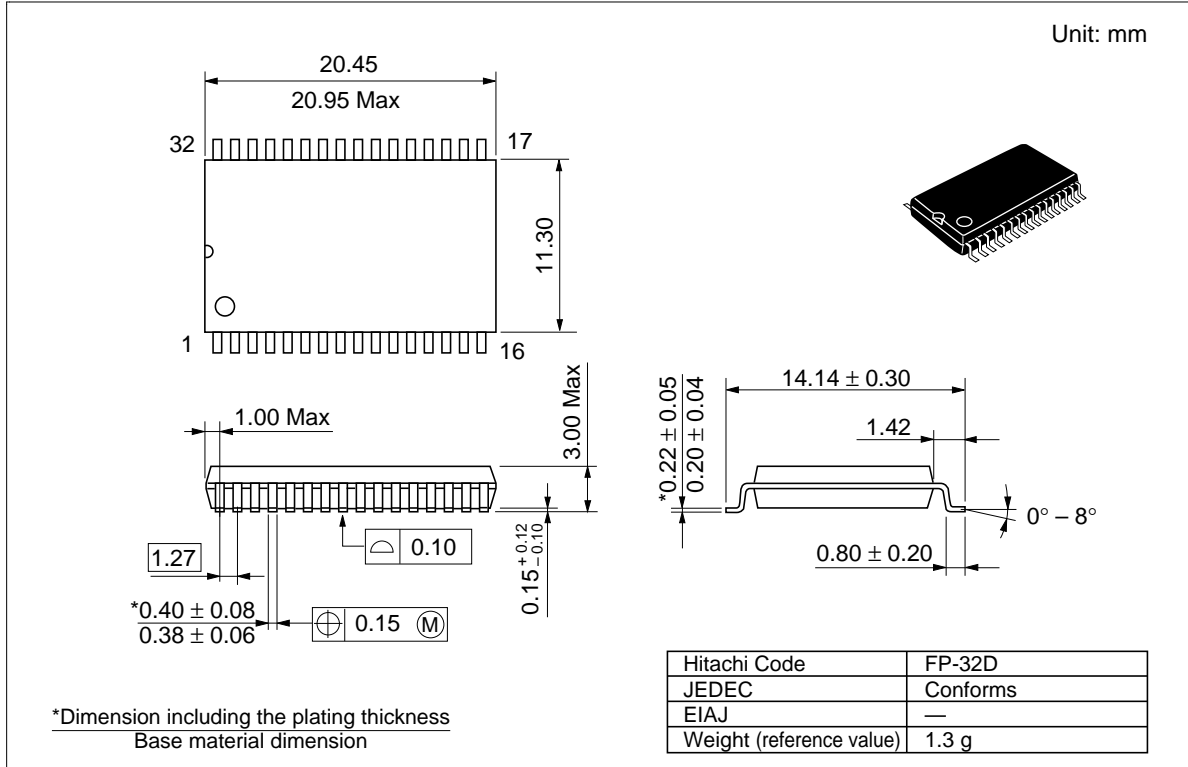
Low  $V_{CC}$  Data Retention Timing Waveform (2) (CS2 Controlled)





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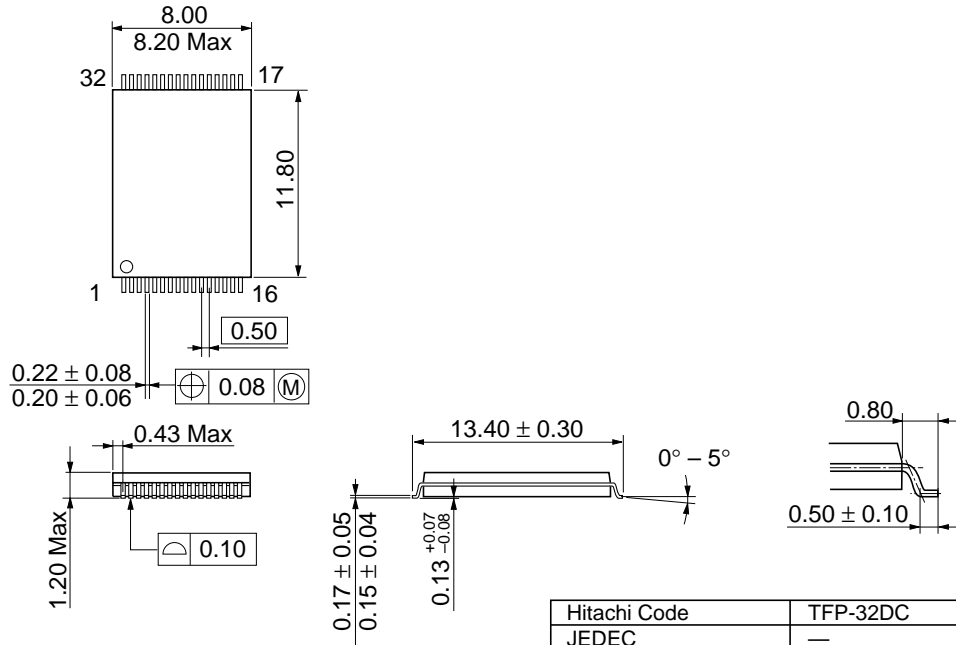
## HM628128DLFP Series (FP-32D)



# HM628128D Series

## HM628128DLTS Series (TFP-32DC)

Unit: mm



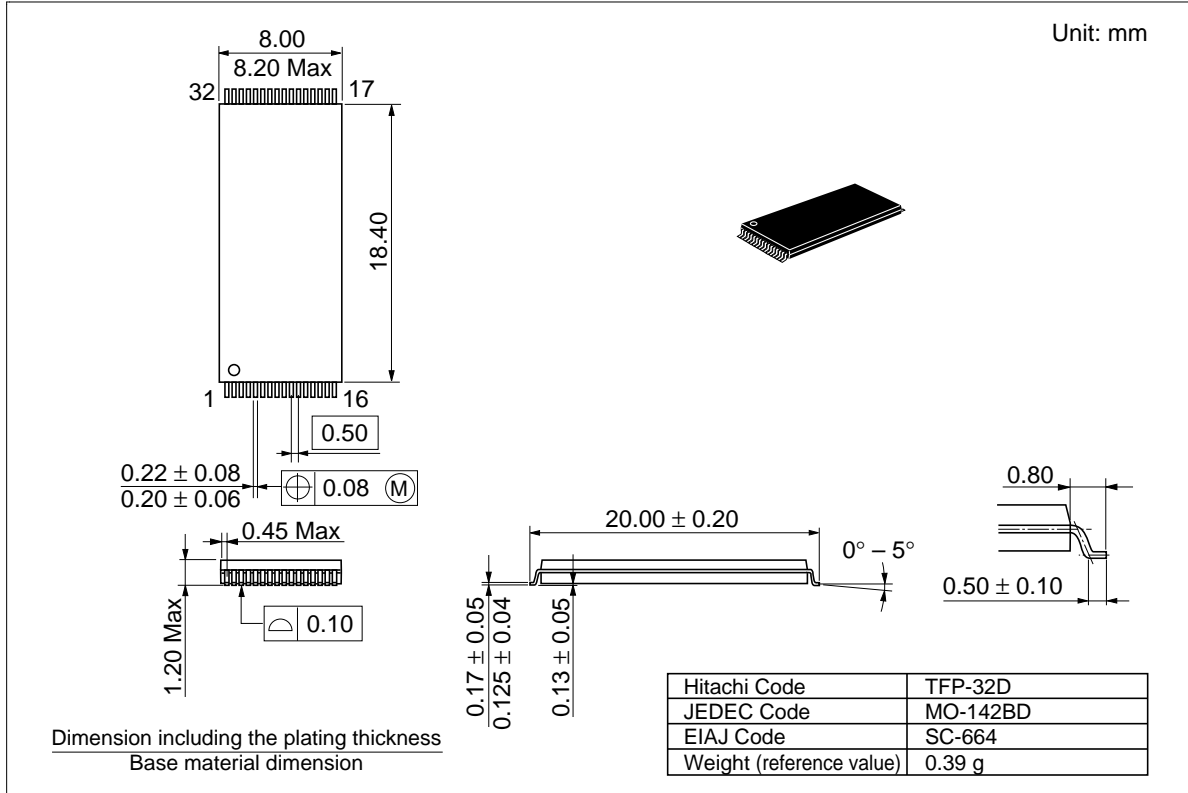
Dimension including the plating thickness  
Base material dimension

Hitachi Code	TFP-32DC
JEDEC	—
EIAJ	—
Weight (reference value)	0.23 g



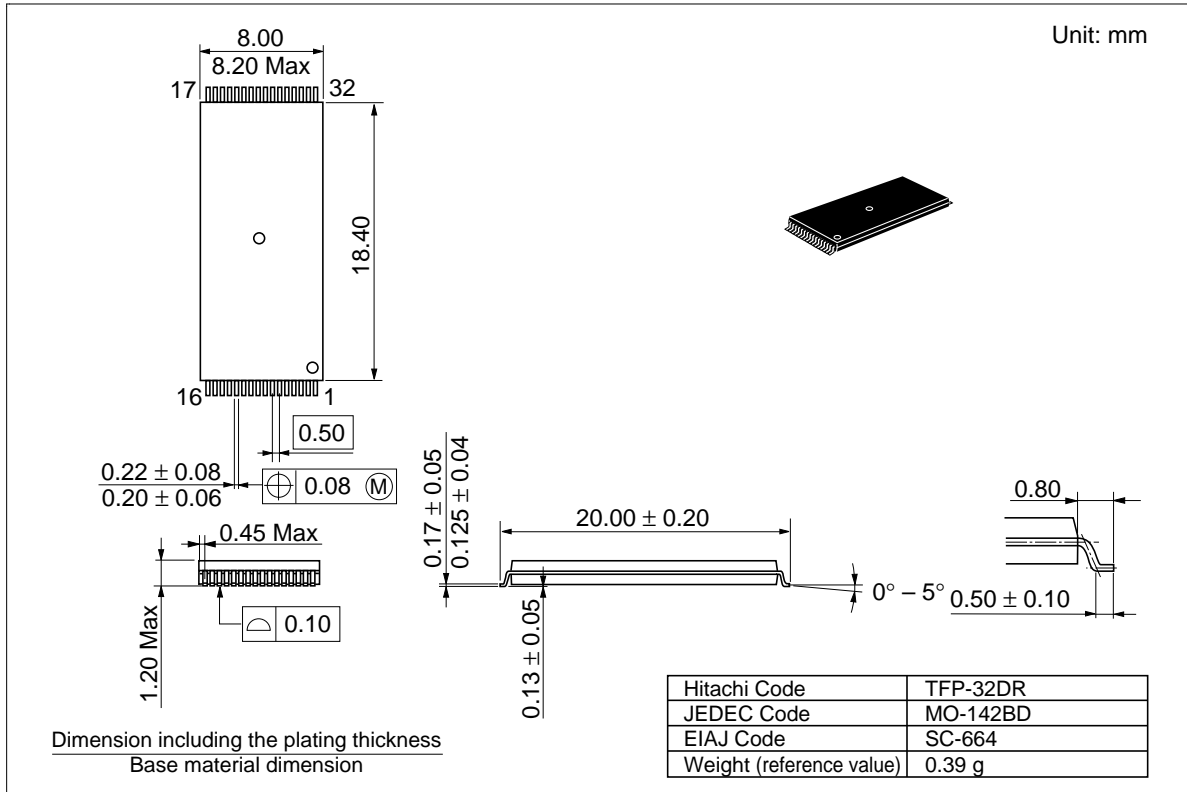
# HM628128D Series

## HM628128DLT Series (TFP-32D)



# HM628128D Series

## HM628128DLR Series (TFP-32DR)



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## HM628128D Series

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### Revision Record

Rev.	Date	Contents of Modification	Drawn by	Approved by
0.0	Jan. 20, 1999	Initial issue		

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